

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
9 December 2004 (09.12.2004)

PCT

(10) International Publication Number
WO 2004/107409 A3

(51) International Patent Classification⁷: **H01L 21/331**,
21/8222, 27/082

Irvine, CA 92606 (US). **RING, Kenneth**; 13406 Heritage
Way #464, Tustin, CA 92782 (US).

(21) International Application Number:
PCT/US2004/008051

(74) Agent: **FARJAMI, Michael**; Farjami & Farjami LLP,
26522 La Alameda Ave., Suite 360, Mission Viejo, CA
92691 (US).

(22) International Filing Date: 17 March 2004 (17.03.2004)

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/442,449 21 May 2003 (21.05.2003) US

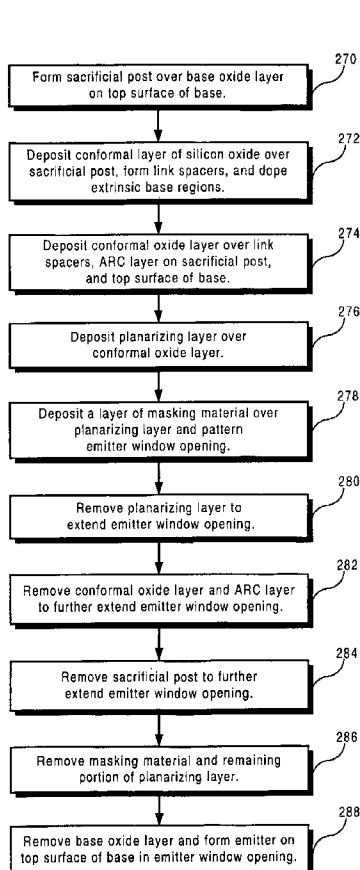
(71) Applicant: **NEWPORT FAB, LLC DBA JAZZ SEMI-
CONDUCTOR** [US/US]; 4321 Jamboree Road, Newport
Beach, CA 92660 (US).

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),

(72) Inventors: **KALBURGE, Amol**; 4371 Rafael St., Irvine,
CA 92604 (US). **YIN, Kevin, Q.**; 28 Santa Cruz Aisle,

[Continued on next page]

(54) Title: METHOD FOR FABRICATING A SELF-ALIGNED BIPOLAR TRANSISTOR HAVING INCREASED MANUFAC-
TURABLY AND RELATED STRUCTURE



(57) Abstract: According to one exemplary embodiment, a bipolar transistor comprises a base having a top surface. The bipolar transistor further comprises a base oxide layer situated on top surface of the base. The bipolar transistor further comprises a sacrificial post situated on base oxide layer. The bipolar transistor further comprises a conformal layer situated over the sacrificial post and top surface of the base, where the conformal layer has a density greater than a density of base oxide layer. The conformal layer may be, for example, HDPCVD oxide. According to this exemplary embodiment, the bipolar transistor further comprises a sacrificial planarizing layer situated over the conformal layer. The sacrificial planarizing layer has a first thickness in a first region between first and second link spacers and a second thickness in a second region outside of first and second link spacers, where the second thickness is generally greater than the first thickness.

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Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

(88) Date of publication of the international search report:
14 July 2005

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.